FORM PTO-1449 (Modified)	Attorney Docket No.: A524R1/T289	Application No.: 09/187,551
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Applicant: MUSAKA et al.	
	Filing Date: November 5, 1998	Group: 1762

Reference Designation — **U.S. PATENT DOCUMENTS** — Page 1

Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
AA	5,462,899	10/31/95	Ikeda	438	238	11/30/93
AB	5,429,995	07/04/95	Nishiyama et al.	437	238	07/16/93
AC	5,420,075	05/30/95	Homma et al.	437	195	04/14/93
AD	5,413,967	05/09/95	Matsuda et al.	437	235	05/03/94
AE	5,407,529	04/18/95	Homma	156	643	03/04/93
AF	5,403,630	04/04/95	Matsui et al.	427	583	10/27/93
AG	5,399,529	03/21/95	Homma	437	195	05/26/93
AH	5,385,763	01/31/95	Okano et al.	427	572	03/01/94
AI	5,356,722	10/18/94	Nguyen et al.	427	569	06/10/92
AJ	5,334,552	08/02/94	Homma	437	195	11/24/92
AK	5,319,247	06/07/94	Matsuura	257	760	10/25/91
AL	5,288,518	02/22/94	Homma	427	255.1	06/05/92
AM	5,286,518	02/15/94	Cain, et al.	427	96	04/30/92
AN	5,279,865	01/18/94	Chebi et al.	427	574	06/28/91
AO	5,275,977	01/04/94	Otsubo et al.	437	235	03/14/91
AP	5,223,457	06/29/93	Mintz, et al.	437	225	10/11/91
AQ	5,215,787	06/01/93	Homma	427	248.1	01/14/92
AR	5,206,060	04/27/93	Balian, et al.	427	489	08/09/90
AS	5,156,881	10/20/92	Okano et al.	427	572	04/16/91
AT	5,013,691	05/07/91	Lory et al.	437	238	07/31/89
AU	4,894,352	01/16/90	Lane et al.	437	238	10/26/88
AV	4,872,947	10/10/89	Wang et al.	156	643	10/26/88
AW	4,851,370	07/25/89	Doklan et al.	437	225	12/28/87
AX	4,818,563	04/04/89	Ishihara et al.	427	55	02/20/86
AY	4,778,721	10/18/88	Sliemers et al.	428	336	07/09/86
AZ	4,668,365	05/26/87	Foster et al.	204	192.23	10/25/84
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BB ✓	4,282,267	08/04/81	Küyel	427	38	03/05/80

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BC	4-239750	08/27/92	JP	H01 L21	90	No (abstract only)
BD	4-341568	11/27/92	JP	C23C 16	40	No (abstract only)
BE	J6 1276-977-A	12/06/86	JP	C23C 16	50	No (abstract only)
BF ✓	WO 92/20833	11/26/92	PCT Weise	C23C	16/00	yes

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

BG	Carl et al., "The Effect of 0_2:C_2F_6 Ratios and Low Frequency Power On The Gap Fill Properties And Stability Of F-TEOS Films", DUMIC Conference, Feb. 1995, pp. 234-240.
BH	Chang et al., "Frequency Effects and Properties of Plasma Deposited Fluorinated Silicon Nitride", J. Vac. Sci. Technol. B6 (2) 1988, pp. 524-532. March/April
BI	Fukada et al., "Preparation Of SiOF Films With Low Dielectric Constant By ECR Plasma CVD", DUMIC Conference, Feb. 1995, pp. 43-49.
BJ	Galiano et al., "Stress-Temperature Behavior of Oxide Films Used For Intermetal Dielectric Applications", VMIC Conference, June 1992, pp. 100-106.
BK	Hayasaka et al., "High-Quality And Low Dielectric Constant SiO_2 CVD Using High Density Plasma", 1993 Dry Process Symposium, ~~Nov. 1994~~, pp. 163-168. Nov. 1-2, 1993
BL	Hoff et al., "Thermal Oxidation Of Silicon In An Afterglow Gas", (undated), Ctr. for Elect. Materials and Devices, Penn State Univ. - no date, but after 1987 (drawings)
BM	Laxman, Ravi K. "Low ε Dielectrics: CVD Fluorinated Silicon Dioxides", Semiconductor International, May 1995, pp. 71-74.
BN	Matsuda et al., "Dual Frequency Plasma CVD Fluorosilicate Glass Deposition For 0.25 μm Interlevel Dielectrics", DUMIC Conference, Feb. 1995, pp. 22-28.
BO	Musaka et al., "Single Step Gap Filling Technology For Subhalf Micron Metal Spacings On Plasma Enhanced TEOS/0_2 Chemical Vapor Deposition System", Extended Abstracts of the 1993 International Conference on Solid State Devices and Materials, Makuhari, 1993, pp. 510-512. No month
BP	Qian et al., "High Density Plasma Deposition And Deep Submicron Gap Fill With Low Dielectric Constant SIOF Films", DUMIC Conference, Feb. 1995, pp. 50-56.
BQ	Robles et al., "Effects of RF Frequency and Deposition Rates on the Moisture Resistance of PECVD TEOS-Based Oxide Films", Vol. 92-1, ECS Extended Abstracts, p. 215, Abstract 129, May 1992.
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BT	Webb et al., "Silicon Dioxide Films Produced By PECVD of TEOS and TMCTS", Proceedings of the Int. Symp. on Ultra Large Scale Integration Science and Technology, No. 9, 1989, Pennington, N.J., pp. 571-585. no month
BU	Yu et al., "Step Coverage Study of Peteos Deposition For Intermetal Dielectric Applications", VMIC Conference, Jun. 1990, 166-172.
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BY	Schravendijk et al., "Correlation Between Dielectric Reliability and Compositional Characteristics of PECVD Oxide Films" VMIC Conference 1992 ISMIC-101/92/0372, June 1992, pp. 372-378.
BZ	Homma et al., "A Room Temperature CVD Technology for Interlayer in Deep-Submicron Multilevel Interconnection" IEEE International Electron Devices Meeting, Washington, D.C., 1991, pp10.7.1-10.7.4. no month
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.